





20V LOW V_{CE(SAT)} PNP SURFACE MOUNTED TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (ZXTN26020DMF)
- Low Collector-Emitter Saturation Voltage, V_{CE(SAT)}
- High Current Gain (hFE) at High IC
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Qualified to AEC-Q101 Standards for High Reliability
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

Mechanical Data

- Case: DFN1411-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)

Applications

- MOSFET and IGBT gate driving
- DC-DC conversion
- Interface between low voltage IC and Load
- Load disconnect switch



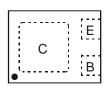




Bottom view



Device Symbol



Pin-Out Top view

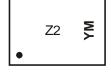
Ordering Information

Product	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP26020DMFTA	7	8	3000

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



Z2= Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2010	2011		2012	2013		2014	2015		2016
Code	W		Χ	Y		Z	Α		В	С		D
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D





Maximum Ratings

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-1.25	Α
Peak Pulse Current	I _{CM}	-4	А
Base Current(DC)	I _B	-0.3	Α
Peak Base Current	I _{BM}	-0.6	А

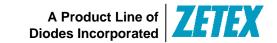
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	1	W
Power Dissipation (Note 4)	P _D	380	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{\theta JA}$	330	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- Device mounted on FR-4 PCB with 1inch square pads.
 Device mounted on FR-4 PCB with minimum recommended pad layout





Electrical Characteristics (at T_A = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	_	_	V	$I_C = -100 \mu A, I_E = 0A$
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	-20	_	_	V	$I_C = -10 \text{mA}, I_B = 0 \text{A}$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-7	_	_	V	$I_E = -100 \mu A, I_C = 0A$
Collector Cutoff Current	Icbo	_	_	-100 -0.5	nA μA	V _{CB} = -20V, I _E = 0A V _{CB} = -20V, I _E = 0A,T _A = 125°C
Emitter Cutoff Current	Ices	_	_	-100	nA	V _{CE} = -20V, V _{BE} = 0V
Base Cutoff Current	lebo	_	_	-50	nA	$V_{BE} = -6V, I_{C} = 0A$
DC Current Gain (Note 5)	h _{FE}	300 235 175 140	_ _ _		_	V _{CE} = -2V, I _C = -100mA V _{CE} = -2V, I _C = -0.5A V _{CE} = -2V, I _C = -1A V _{CE} = -2V, I _C = -1.5A
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(SAT)}	_ _ _ _	_ _ _ _	-80 -100 -155 -235	mV mV mV	$I_C = -100$ mA, $I_B = -1$ mA $I_C = -500$ mA, $I_B = -50$ mA $I_C = -1$ A, $I_B = -50$ mA $I_C = -1.25$ A, $I_B = -62.5$ mA
Equivalent On-Resistance	R _{CE(SAT)}	_	125	_	mΩ	$I_C = -1A$, $I_B = -50mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	-1.1	V	V _{CE} = -5V, I _C = -1A
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.15	V	$I_C = -1A$, $I_B = -50mA$
Output Capacitance (Note 5)	C _{obo}	_	_	20	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	200	_	_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Turn-On Time	t _{on}	_	60	_	ns	
Delay Time	t _d	_	20	_	ns	
Rise Time	t _r	_	40	_	ns	$V_{CC} = -10V, I_{C} = -1A$
Turn-Off Time	t _{off}	_	167	_	ns	$I_{B2} = -I_{B1} = -50 \text{mA}$
Storage Time	t _s	_	140	_	ns	
Fall Time	t _f	_	27	_	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.



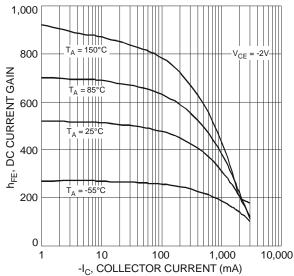
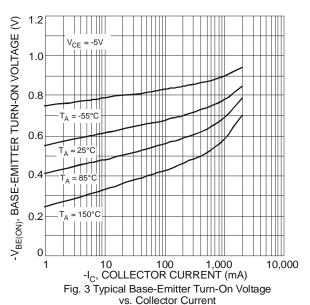


Fig. 1 Typical DC Current Gain vs. Collector Current



1,000 f = 1MHz CAPACITANCE (pF) 100 10 1 0.1 10 100 V_R, REVERSE VOLTAGE (V) Fig. 5 Typical Capacitance Characteristics

-V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 0.1 -55°C 0.01 0.001 0.1 10 100 1,000 10,000 -I_C, COLLECTOR CURRENT (mA)
Fig. 2 Typical Collector-Emitter Saturation Voltage

vs. Collector Current

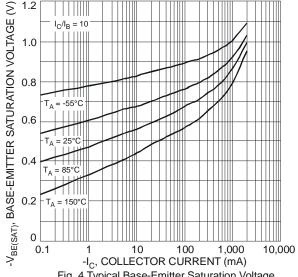
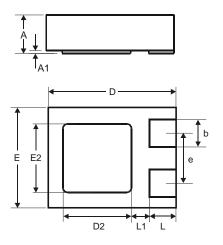


Fig. 4 Typical Base-Emitter Saturation Voltage vs. Collector Current



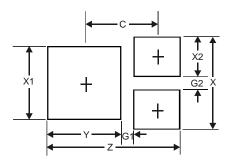


Package Outline Dimensions



DFN1411-3						
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0	0.05	0.02			
b	0.25	0.35	0.30			
D	1.35	1.475	1.40			
D2	0.65	0.85	0.75			
Е	1.05	1.18	1.10			
E2	0.65	0.85	0.75			
е	_	_	0.55			
L	0.225	0.325	0.275			
L1	_	_	0.20			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.38
G1	0.15
G2	0.15
X	0.95
X1	0.75
X2	0.40
Y	0.75
C	0.76





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